

## PATENT ABSTRACTS OF JAPAN

(11) Publication number:

64-064318

(43) Date of publication of application: 10.03.1989

(51) Int. CI.

H01L 21/285

(21) Application number: 62-220144

(71) Applicant: HITACHI LTD

(22) Date of filing:

04.09.1987

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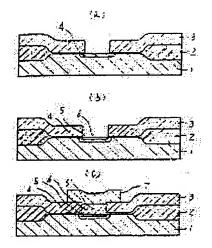
SAITO MASAYOSHI SUZUKI MASAYASU

## (54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To completely fill a contact hole with W by forming a tungsten silicide or tungsten/tungsten silicide film on an Si by a reaction of WF6 with the Si at the initial of the reaction, and then growing a W film by H2 reducing reaction of the WF6 thereon.

CONSTITUTION: A phosphorus glass film 3 is deposited on a thermal oxide film 2 on a P-type silicon crystalline substrate 1. Then, after 1 contact hole is formed at the film 3. As ions are implanted, and heated to form an N+ type high concentration diffused layer 4 in the contact hole. A tungsten film 6/tungsten silicide film 5 are firmed by a low pressure CVD method with WF6 and N2 on the contact. Thereafter, a tungsten film 6' is further grown on the contact by a low pressure CVD method with the WF6 and H2. Subsequently, aluminum electrodes 7 are formed. Similar result can be obtained by employing a CVD oxide film silicon nitride, BPSG, SOG, etc., instead of the film 3.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection

[Date of extinction of right]

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## @ EPODOC / EPO

PN - JP1/064318 A 19890310

PD - 1989-03-10

PR - JP19870220144 19870904

OPD - 1987-09-04

TI - MANUFACTURE OF SEMICONDUCTOR DEVICE

IN - KOBAYASHI NOBUYOSHI;SAITO MASAYOSHI;SUZUKI MASAYASU

PA - HITACHI LTD

IC - H01L21/285

@ WPI / DERWENT

 Tungsten electrode burying method - by CVD of tungsten hexa:fluoride to form deposited tungsten using reaction with hydrogen NoAbstract Dwg 2/2

PR - JP19870220144 19870904

PN - JP1064318 A 19890310 DW198916 010pp

PA - (HITA) HITACHI LTD

IC - H01L21/28

OPD - 1987-09-04

AN - 1989-118503 [16]

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PN - JP1064318 A 19890310

PD - 1989-03-10

AP - JP19870220144 19870904

IN - KOBAYASHI NOBUYOSHI; others:02

PA - HITACHI LTD

TI - MANUFACTURE OF SEMICONDUCTOR DEVICE

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